

2A Sink/Source Bus Termination Regulator

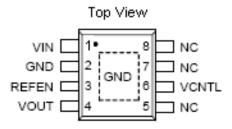
Description

The SE9174C is a simple, cost-effective and high-speed linear regulator designed to generate termination voltage in double data rate (DDR) memory system to comply with the JEDEC SSTL 2 and SSTL 18 or other specific interfaces such as HSTL, SCSI-2 SCSI-3 and etc. devices requirements. The regulator is capable of actively sinking or sourcing up to 2A while regulating an output voltage to within 40mV. The output termination voltage cab be tightly regulated to track 1/2VDDQ by two external voltage divider resistors or the desired output voltage can be pro-grammed by externally forcing the REFEN pin voltage.

The SE9174C also incorporates a high-speed differential amplifier to provide ultra-fast response in line/load transient. Other features include extremely low initial offset voltage, excellent load regulation, current limiting in bi-directions and on-chip thermal shut-down protection.

The SE9174C are available in the PSOP-8 (Exposed Pad) surface mount packages.

Pin Configuration





Pin Description

Pin Name	Pin function		
V _{IN}	Power Input		
GND	Ground		
V _{CNTL}	Gate Drive Voltage		
REFEN	Reference Voltage input and Chip Enable		
V _{OUT}	Output Voltage		

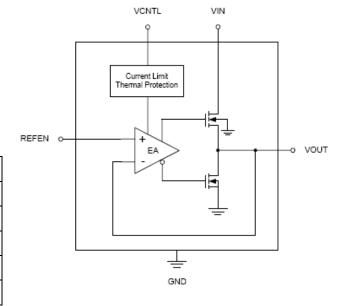
Features

- Ideal for DDR-I, DDR-II and DDR-III V_{TT} Applications
- Sink and Source 2A Continuous Current
- Integrated Power MOSFETs
- Generates Termination Voltage for SSTL_2, SSTL _18, HSTL, SCSI-2 and SCSI-3 Interfaces.
- High Accuracy Output Voltage at Full-Load
- Output Adjustment by Two External Resistors
- Low External Component Count
- Shutdown for Suspend to RAM (STR) Functionality with High-Impedance Output
- Current Limiting Protection
- On-Chip Thermal Protection
- Available in PSOP-8 (Exposed Pad) Packages
- V_{IN} and V_{CNTL} No Power Sequence Issue
- > 100% Lead (Pb)-Free

Application

- Desktop PCs, Notebooks, and Workstations
- Graphics Card Memory Termination
- > Set Top Boxes, Digital TVs, Printers
- Embedded Systems
- Active Termination Buses
- DDR-I, DDR-II and DDR-III Memory Systems

Block Diagram



Revision 12/4/2008



Absolute Maximum Rating (1)

Parameter	Symbol	Value	Unit
Input Voltage	V _{IN}	6	V
Control Voltage	V _{CNTL}	6	V
Power Dissipation	P _D	Internally Limited	
ESD Rating		3	KV
Storage Temperature Range	Ts	-65 to 150	°C
Lead Temperature (Soldering, 5 sec.)	T _{LEAD}	260	°C
Package Thermal Resistance	Θ_{JC}	28	°C/W

Operating Rating⁽²⁾

Parameter	Symbol	Value	Units
Input Voltage	V _{IN}	2.5 to 1.5 \pm 3%	V
Control Voltage	V _{CNTL}	5.0 or 3.3 \pm 5%	V
Ambient Temperature	T _A	-40 to +85	°C
Junction Temperature	TJ	-40 to +125	°C

Electrical Characteristics

 $V_{\text{IN}}=2.5\text{V}/1.8\text{V}/1.5\text{V}, V_{\text{CNTL}}=3.3\text{V}, V_{\text{REFEN}}=1.25\text{V}/0.9\text{V}/0.75\text{V}, C_{\text{OUT}}=10\mu\text{F} \text{ (Ceramic)}), T_{\text{A}}=25^{\circ}\text{C}, \text{ unless otherwise specified}$

Parameter	Symbol	Test Conditions		Тур	Max	Units	
Input							
VCNTL Operation Current	I _{CNTL}	I _{OUT} =0A		1	2.5	mA	
Standby Current	I _{STBY}	$V_{\text{REFEN}} < 0.2V$ (Shutdown), R_{LOAD} = 180 Ω		50	90	μA	
Output (DDR / DDR II / DDR III)							
Output Offset Voltage ⁽³⁾	V _{OS}	I _{OUT} = 0A	-20		+20	mV	
Load Regulation ⁽⁴⁾	ΔV_{LOAD}	I _{OUT} = +2A			+20		
		I _{OUT} = -2A					
Protection							
Current limit	I _{LIM}		2.2			Α	
Thermal Shutdown Temperature	T _{SD}	$3.3V \le V_{CNTL} \le 5V$		170		°C	
Thermal Shutdown Hysteresis	ΔT_{SD}	$3.3V \le V_{CNTL} \le 5V$		35			
REFEN Shutdown							
Shutdown Threshold	V _{IH}	Enable				V	
	V _{IL}	Shutdown			0.2		

Note 1: Exceeding the absolute maximum rating may damage the device.

Note 2: V_{OS} offset is the voltage measurement defined as V_{OUT} subtracted from V_{REFEN}

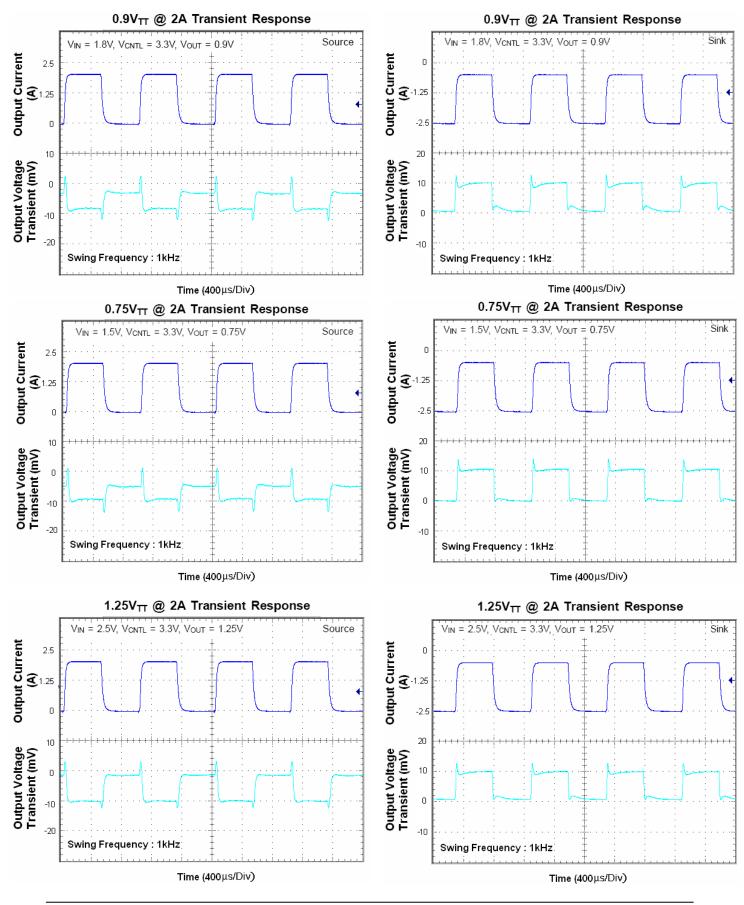
Note 3: V_{OS} offset is the voltage measurement defined as V_{OUT} subtracted from V_{REFEN} .

Note 4: Regulation is measured at constant junction temperature by using a 5ms current pulse. Devices are tested for load

regulation in the load range from 0A to 2A.



Typical Operating Characteristics



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Application Information

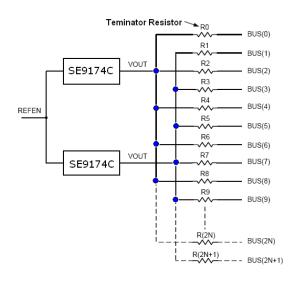
Input Capacitor and Layout Consideration

Place the input bypass capacitor as close as possible to the SE9174C. A low ESR capacitor larger than 470uF is recommended for the input capacitor. Use short and wide traces to minimize parasitic resistance and inductance.

Inappropriate layout may result in large parasitic inductance and cause undesired oscillation between SE9174C and the preceding power converter.

Consideration while designs the resistance of voltage divider

Make sure the sinking current capability of pull-down NMOS if the lower resistance was chosen so that the voltage on VREFEN is below 0.2V. In addition, the capacitor and voltage divider form the lowpass filter. There are two reasons doing this design; one is for output voltage soft-start while another is for noise immunity.



Thermal Consideration

SE9174C regulators have internal thermal limiting circuitry designed to protect the device during overload conditions.For continued operation, do not exceed maximum operation junction temperature 125° C. The power dissipation definition in device is: PD = (VIN - VOUT) x IOUT + VIN x IQ

The maximum power dissipation depends on the thermal resistance of IC package, PCB layout, the rate of surroundings airflow and temperature difference between junction to ambient. The maximum power dissipation can be calculated by following formula:

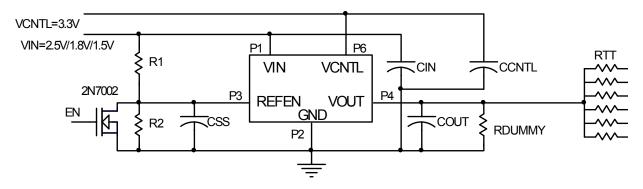
 $P_{D(MAX)} = (T_{J(MAX)} - T_A) / \Theta J_A$

Where $T_{J(MAX)}$ is the maximum operation junction temperature 125°C, TA is the ambient temperature and the Θ JA is the junction to ambient thermal resistance. The junction to ambient thermal resistance (Θ JA is layout dependent) for PSOP-8 package (Exposed Pad) is 75°C/W on standard JEDEC 51-7 (4 layers, 2S2P) thermal test board. The maximum power dissipation at TA = 25°C can be calculated by following formula: PD(MAX) = (125°C - 25°C) / 75°C/W = 1.33W

The thermal resistance Θ JA of PSOP-8 (Exposed Pad) is determined by the package design and the PCB design. However, the package design has been decided. If possible, it's useful to increase thermal performance by the PCB design. The thermal resistance can be decreased by adding copper under the expose pad of PSOP-8 package. We have to consider the copper couldn't stretch infinitely and avoid the tin overflow.



Application Diagram



 $\mathsf{R}_1 = \mathsf{R}_2 = 100 \mathsf{K} \Omega, \, \mathsf{R}_{\mathsf{T}\mathsf{T}} = 50 \Omega/33 \Omega/25 \Omega$

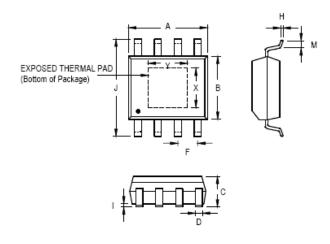
 $C_{OUT, min} = 10 \mu F$ (Ceramic) + 1000 μF under the worst case testing condition

RDUMMY = $1k\Omega$ as for VOUT discharge when VIN is not present but VCNTL is present

 C_{SS} = 1µF, C_{IN} = 470µF(Low ESR), C_{CNTL} = 47µF



Outline Drawing PSOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
А	4.801	5.004	0.189	0.197	
В	3.810	3.988	0.150	0.157	
С	1.346	1.753	0.053	0.069	
D	0.330	0.508	0.013	0.020	
F	1.194	1.346	0.047	0.053	
Н	0.191	0.254	0.008	0.010	
I	0.000	0.152	0.000	0.006	
J	5.791	6.198	0.228	0.244	
м	0.406	1.270	0.016	0.050	
Х	2.057	2.515	0.081	0.099	
Y	2.057	3.404	0.081	0.134	

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